TO-3P

Schottky Barrier Diode in a TO-3P Plastic Package.

Low forward voltage drop, low power losses, High efficiency operation.

OR-ing DC-DC

For use in high frequency inverters, switching pow

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RM} V_{RWM} V_{DC}	150	V
RMS Reverse Voltage	V_{RMS}	105	V
Average forward current	$I_{F(AV)}$	2 15	A
Non-Repetitive Peak Forward Surge Current	I_{FSM}	250	A
Thermal Resistance Junction to Ambient case	$R_{\theta Jc}$	4.6	/W
Operating and Storage Temperature Range	T_j T_{stg}	-40 +150	

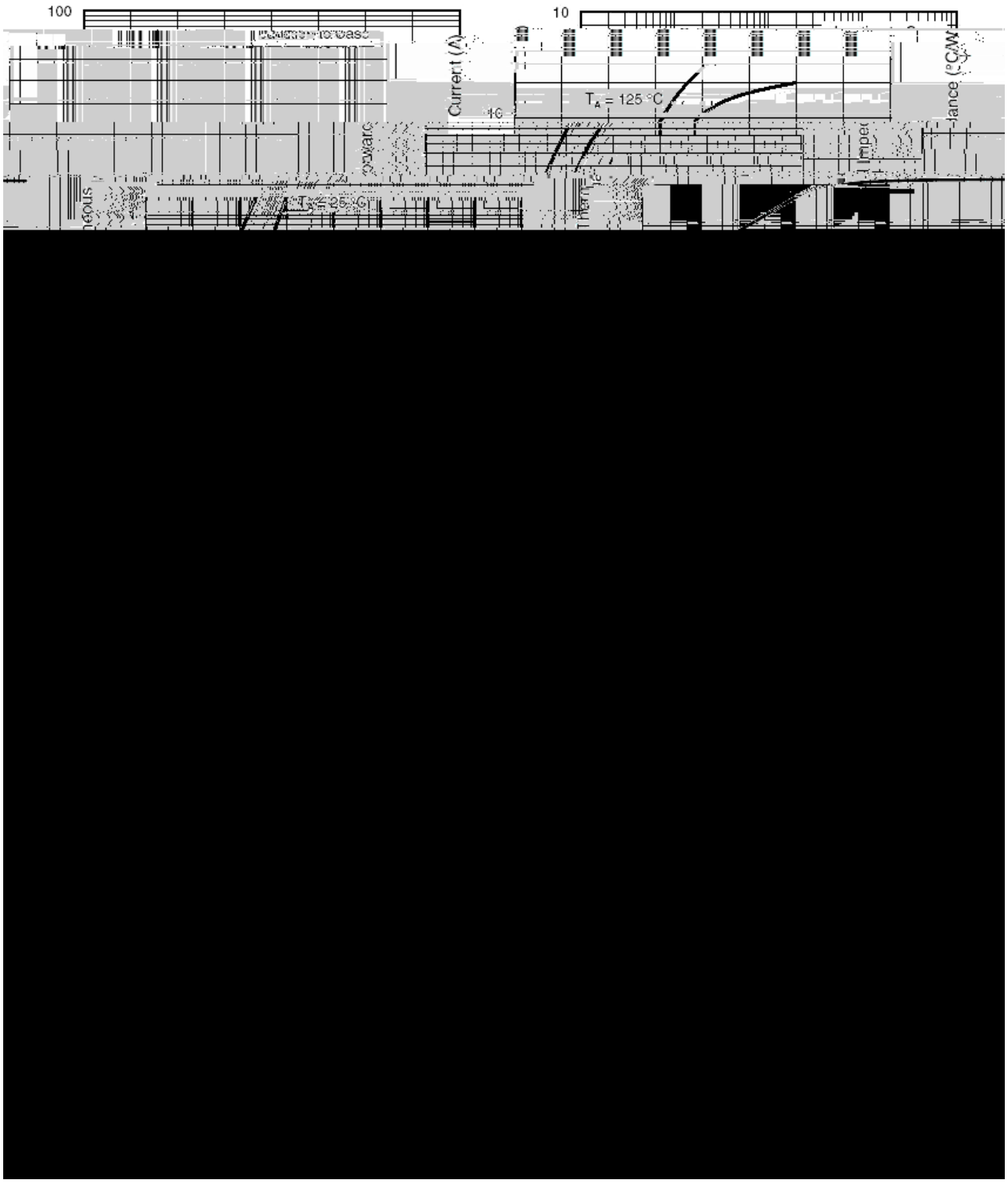
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V_{BR}	I_R=1mA(Ta=25)	150			V
Forward Voltage	V_F	I_F =5A(Ta=25)		0.69	0.75	V
		I_F =10A(Ta=25)		0.76	0.85	V
		I_F =15A(Ta=25)		0.81	0.90	V
		I_F =5A(Ta=125)		0.55		V
		I_F =10A(Ta=125)		0.62		V
		I_F =15A(Ta=125)		0.67	0.75	V
Instantaneous Reverse current (Note 1)	I_R Note 1	V_R=150V(Ta=25)		4	20	μA
		V_R=150V(Ta=125)		5	10	mA

/Notes

1. /Short duration pulse test used to minimize self-heating effect.
2. / Unless otherwise noted, values for the parameters of a single chip.

/ Electrical Characteristic Curve



/ Marking Instructions



BR

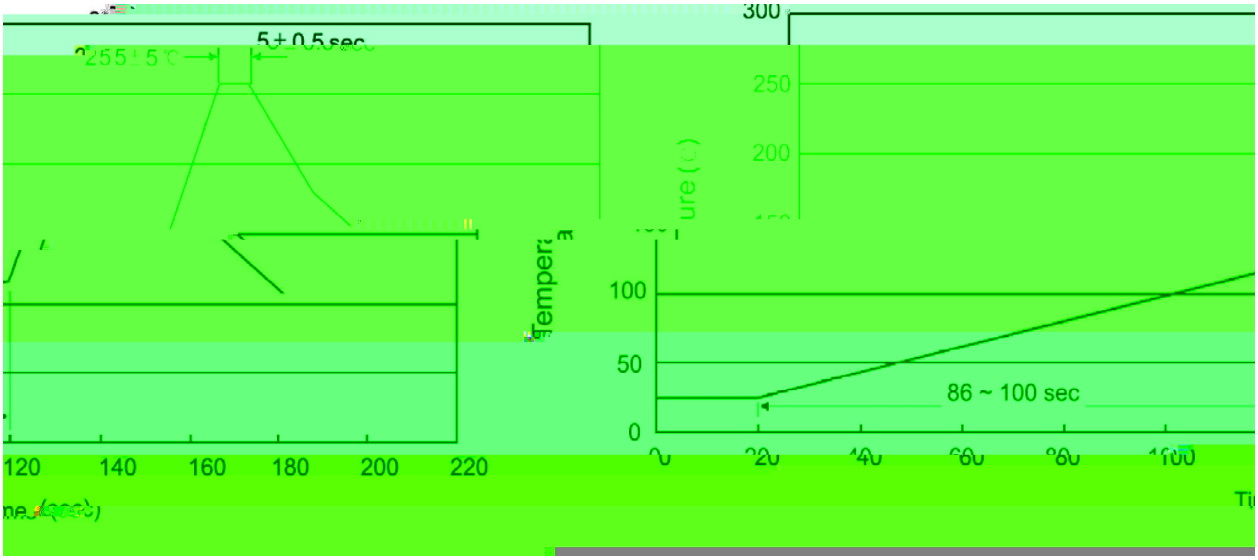
LV30150PT

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Note:

BR:	Company Code.
LV30150PT:	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



					Note:
1		25 150		60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2		255±5		5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3			2 10	/sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ TUBE

Package Type	Units					Dimension		(unit mm^3)
	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box
TO-3P	30	15	450	5	2250	497.5×46×8	555×164×50	575 290 180

/ Notices